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N-Channel 80 V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (TYP.)	
80	0.0021 at V _{GS} = 10 V	200	168 nC	
	0.0027 at V _{GS} = 4.5 V	180	100110	

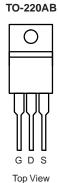
FEATURES

- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested



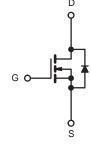
APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management



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SEMICONDUCTOR



N-Channel MOSFE

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	80	V		
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C		200		
	T _C = 125 °C	— I _D	140		
Pulsed Drain Current (t = 100 μs)		I _{DM}	800	А	
Avalanche Current	L = 0.1 mH	las	190		
Single Avalanche Energy ^a	L = 0.1 IIII	E _{AS}	1925	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	В	300 b	W	
	T _C = 125 °C	$ P_D$	125 ^b		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	2.1	°C ///	
Junction-to-Case (Drain)	R _{thJC}	0.5	°C/W	

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80	-	-	\/
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	-	3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	- μΑ
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 80 V, V_{GS} = 0 V, T_J = 125 °C	-	-	100	
-		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$	-	-	2	mA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	200	-	-	Α
Drain Source On State Besistance	D-	V _{GS} = 10 V, I _D = 30 A	-	0.0021	0.0027	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 30 \text{ A}$	-	0.0028	0.0036	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A	-	90	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz	-	10500	-	pF
Output Capacitance	C _{oss}		-	1650	-	
Reverse Transfer Capacitance	C _{rss}		-	75	-	
Total Gate Charge ^c	Q_g		-	168		nC
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	55	-	
Gate-Drain Charge ^c	Q_{gd}		-	23	-	
Gate Resistance	R_g	f = 1 MHz		2.3		Ω
Turn-On Delay Time ^c	t _{d(on)}		-	28	-	
Rise Time ^c	t _r	V_{DD} = 50 V, R_L = 1.67 Ω I_D \cong 30 A, V_{GEN} = 10 V, R_g = 1 Ω	-	75	-	ns
Turn-Off Delay Time ^c	t _{d(off)}		-	88	-	
Fall Time ^c	t _f		-	32	-	
Drain-Source Body Diode Ratings a	nd Characteri	stics ^b (T _C = 25 °C)				
Pulsed Current (t = 100 μs)	I _{SM}		-	-	800	Α
Forward Voltage ^a	V _{SD}	I _F = 30 A, V _{GS} = 0 V	-	0.7	1.2	V
Reverse Recovery Time	t _{rr}	I _F = 30 A, di/dt = 100 A/μs	-	118	-	ns
Peak Reverse Recovery Charge	I _{RM(REC)}		-	5	10	Α
Reverse Recovery Charge	Q_{rr}		-	305	-	μC

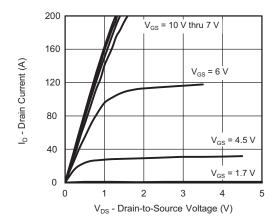
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

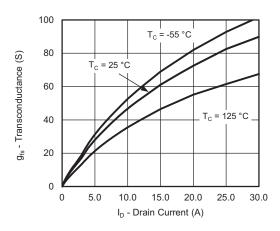
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



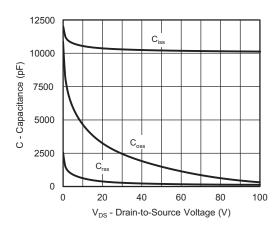
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



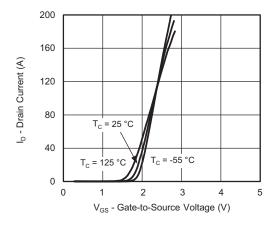
Output Characteristics



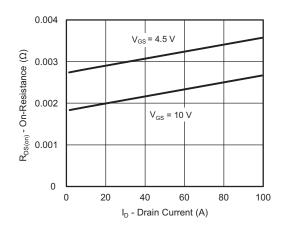
Transconductance



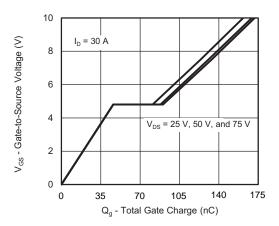
Capacitance



Transfer Characteristics



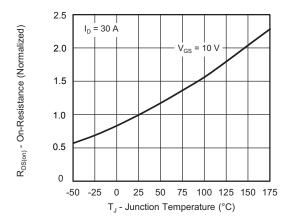
On-Resistance vs. Drain Current



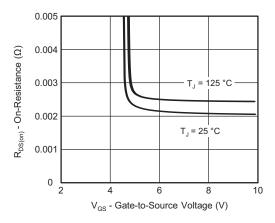
Gate Charge



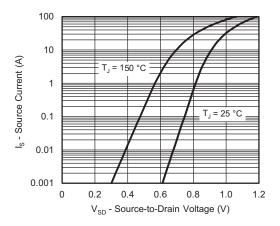
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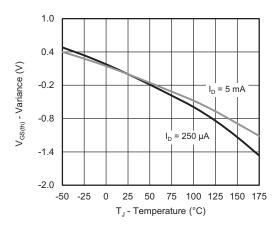
On-Resistance vs. Junction Temperature



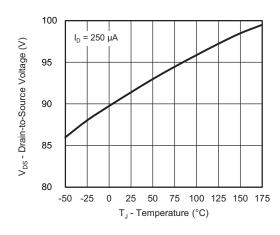
On-Resistance vs. Gate-to-Source Voltage



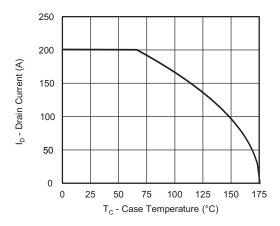
Source Drain Diode Forward Voltage



Threshold Voltage



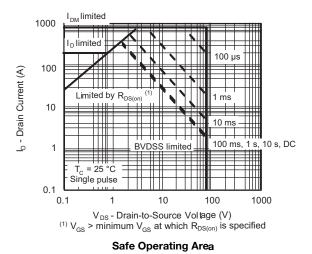
Drain Source Breakdown vs. Junction Temperature

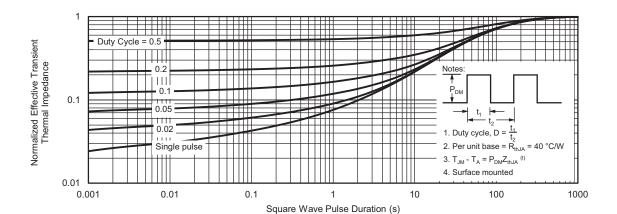


Current De-Rating



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)





Normalized Thermal Transient Impedance, Junction-to-Ambient





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